Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"20050047211"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 16:47
L2	38243	serrated	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 16:48
L3	719	serrated and capacitor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 16:49
L4	261	3 and program\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 16:49
L5	24	4 and EEPROM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 16:52
L6	71553	EEPROM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 16:52
L7	76130	flash near memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 16:52
L8	38	programming adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 16:58
L9	7762	program\$7 with capacitor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 16:59

L10	963	9 and polysilicon	US-PGPUB; USPAT; EPO; JPO;	OR	OFF	2005/05/24 16:59
	·		DERWENT; IBM_TDB			
L11	2	10 and serrated	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:02
L12	1	distributive near EEPROM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:03
L13	0	thin adj oxide adj serrated	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:04
L14	:0	serrated near oxide near region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:04
L15	138	2 near region\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:05
L16	1	15 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:07
L17	29003	Analog near voltage\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:07
L18	1	restriction adj oxide adj growth	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:08
L19	;2	distributive with EEPROM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:10

L20	100	programming near capacitor\$1	US-PGPUB;	OR	OFF	2005/05/24 17:19
		programming fieds capacitor #1	USPAT; EPO; JPO; DERWENT; IBM_TDB		J	2005, 05, 2117115
L21	47	20 and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:10
L22	2	20 and tunnel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:21
L23	38243	serrated	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:22
L24	440	drawing adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:22
L25	;5	23 and 24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:24
L26	100	restrict adj oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:24
L27	2	24 and 26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:30
L28	7762	program\$6 with capacitor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:32
L29	26	28 and serrated	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:35

L30	2	20 and tunnel	US-PGPUB; USPAT; EPO; JPO;	OR	OFF	2005/05/24 17:37
			DERWENT; IBM_TDB			
L31	38243	serrated	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:37
L32	43	serrated adj element	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:46
L33	429	tunneling adj region\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:47
L34		31 and 33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 17:47